IMS1800M CMOS High Performance 256K x 1 Static RAM MIL-STD-883C

Advance Information

FEATURES

- INMOS' Very High Speed CMOS
- Advanced Process - 1.2 Micron Design Rules
- 256K x 1 Bit Organization
- 30, 35 and 45 ns Address Access Times
- 30, 35 and 45 ns Chip Enable Access Times
- Fully TTL Compatible
- Separate Data Input and Outputs
- Three-state Output
- 24 Pin 300-mil DIP and 28 Pin LCC
- Single +5V ± 10% Operation
- Power Down Function

DESCRIPTION

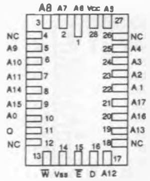
The INMOS IMS1800M is a high performance 256Kx1 CMOS Static RAM. The IMS1800M provides maximum density and speed enhancements with the additional benefits of lower power and superior reliability.

The IMS1800M features fully static operation requiring no external clocks or timing strobes, with equal access and cycle times. Additionally, the IMS1800M provides a Chip Enable function ($\overline{E}$) that can be used to place the device into a low power standby mode.

The IMS1800M is a high speed VLSI RAM intended for military applications which require high performance and superior reliability.

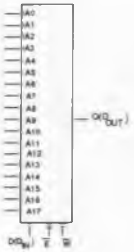
PIN CONFIGURATION

DIP and SOJ

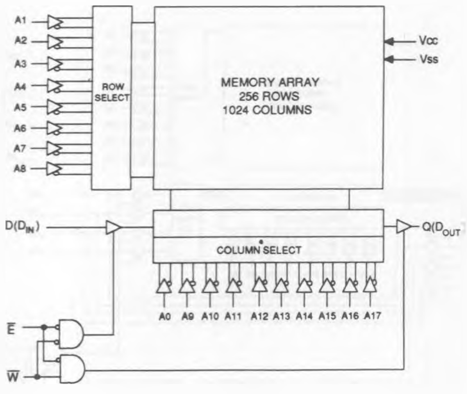


CHIP CARRIER

LOGIC SYMBOL



BLOCK DIAGRAM



PIN NAMES

A_0 - A_{17}	ADDRESS INPUTS	Q	DATA OUT
$\overline{W}$	WRITE ENABLE	Vcc	POWER (+5V)
$\overline{E}$	CHIP ENABLE	Vss	GROUND
D	DATA INPUT		